

Kristoffer Andersson

List of Publications by Year in descending order

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54
papers

959
citations

471061

17
h-index

476904

29
g-index

54
all docs

54
docs citations

54
times ranked

745
citing authors

#	ARTICLE	IF	CITATIONS
1	Design of a Concurrent Dual-Band 1.8–2.4-GHz GaN-HEMT Doherty Power Amplifier. IEEE Transactions on Microwave Theory and Techniques, 2012, 60, 1840-1849.	2.9	126
2	Design of a Highly Efficient 2–4-GHz Octave Bandwidth GaN-HEMT Power Amplifier. IEEE Transactions on Microwave Theory and Techniques, 2010, 58, 1677-1685.	2.9	125
3	Fabrication and characterization of field-plated buried-gate SiC MESFETs. IEEE Electron Device Letters, 2006, 27, 573-575.	2.2	66
4	Thermal Study of the High-Frequency Noise in GaN HEMTs. IEEE Transactions on Microwave Theory and Techniques, 2009, 57, 19-26.	2.9	50
5	An AlGaIn/GaN HEMT-Based Microstrip MMIC Process for Advanced Transceiver Design. IEEE Transactions on Microwave Theory and Techniques, 2008, 56, 1827-1833.	2.9	49
6	An X-Band AlGaIn/GaN MMIC Receiver Front-End. IEEE Microwave and Wireless Components Letters, 2010, 20, 55-57.	2.0	42
7	An SiC MESFET-Based MMIC Process. IEEE Transactions on Microwave Theory and Techniques, 2006, 54, 4072-4078.	2.9	34
8	Branch-Line Coupler Design Operating in Four Arbitrary Frequencies. IEEE Microwave and Wireless Components Letters, 2012, 22, 67-69.	2.0	29
9	A General Statistical Equivalent-Circuit-Based De-Embedding Procedure for High-Frequency Measurements. IEEE Transactions on Microwave Theory and Techniques, 2008, 56, 2692-2700.	2.9	28
10	Fast Multiharmonic Active Load–Pull System With Waveform Measurement Capabilities. IEEE Transactions on Microwave Theory and Techniques, 2012, 60, 149-157.	2.9	28
11	A Single-Ended Resistive X-Band AlGaIn/GaN HEMT MMIC Mixer. IEEE Transactions on Microwave Theory and Techniques, 2008, 56, 2201-2206.	2.9	25
12	Electrothermal Access Resistance Model for GaN-Based HEMTs. IEEE Transactions on Electron Devices, 2011, 58, 466-472.	1.6	24
13	Concurrent dual-band GaN-HEMT power amplifier at 1.8 GHz and 2.4 GHz. , 2012, , .		21
14	Combined TiN- and TaN temperature compensated thin film resistors. Thin Solid Films, 2012, 520, 2162-2165.	0.8	21
15	Improvement of Oscilloscope Based RF Measurements by Statistical Averaging Techniques. , 2006, , .		19
16	Accurate Phase-Noise Prediction for a Balanced Colpitts GaN HEMT MMIC Oscillator. IEEE Transactions on Microwave Theory and Techniques, 2013, 61, 3916-3926.	2.9	18
17	A highly linear double balanced Schottky diode S-band mixer. IEEE Microwave and Wireless Components Letters, 2006, 16, 336-338.	2.0	17
18	Electro-thermal simulations of a microwave 4H-SiC MESFET on high purity semi-insulating substrate. Solid-State Electronics, 2007, 51, 1144-1152.	0.8	17

#	ARTICLE	IF	CITATIONS
19	Transient Simulation of Microwave SiC MESFETs With Improved Trap Models. IEEE Transactions on Electron Devices, 2010, 57, 729-732.	1.6	17
20	SiC Varactors for Dynamic Load Modulation of High Power Amplifiers. IEEE Electron Device Letters, 2008, 29, 728-730.	2.2	15
21	Resistive SiC-MESFET mixer. IEEE Microwave and Wireless Components Letters, 2002, 12, 119-121.	2.0	13
22	High-Efficiency Power Amplifier. IEEE Microwave Magazine, 2011, 12, 81-84.	0.7	12
23	Influence of Field Plates and Surface Traps on Microwave Silicon Carbide MESFETs. IEEE Transactions on Electron Devices, 2008, 55, 1875-1879.	1.6	11
24	Oscilloscope based two-port measurement system using error-corrected modulated signals. , 2012, , .		11
25	Design and Fabrication of 4H-SiC RF MOSFETs. IEEE Transactions on Electron Devices, 2007, 54, 3138-3145.	1.6	10
26	A highly efficient 3.5 GHz inverse class-F GaN HEMT power amplifier. International Journal of Microwave and Wireless Technologies, 2010, 2, 317-324.	1.5	10
27	Highly efficient GaN-HEMT power amplifiers at 3.5 GHz and 5.5 GHz. , 2011, , .		10
28	On the Large Signal Evaluation and Modeling of GaN FET. IEICE Transactions on Electronics, 2010, E93-C, 1225-1233.	0.3	9
29	TiN thin film resistors for monolithic microwave integrated circuits. Journal of Vacuum Science and Technology B: Nanotechnology and Microelectronics, 2010, 28, 912-915.	0.6	9
30	Extraction of an Electrothermal Mobility Model for AlGaIn/GaN Heterostructures. IEEE Transactions on Electron Devices, 2012, 59, 3344-3349.	1.6	9
31	Highly Linear Gallium Nitride MMIC LNAs. , 2012, , .		8
32	Investigation of Push-Pull Microwave Power Amplifiers Using an Advanced Measurement Setup. IEEE Microwave and Wireless Components Letters, 2013, 23, 220-222.	2.0	8
33	The Effect of Forward Gate Bias Stress on the Noise Performance of Mesa Isolated GaN HEMTs. IEEE Transactions on Device and Materials Reliability, 2015, 15, 40-46.	1.5	8
34	Multi-band/multi-mode and efficient transmitter based on a Doherty Power Amplifier. , 2012, , .		8
35	Investigation of the Scalability of 4H-SiC MESFETs for High Frequency Applications. Materials Science Forum, 2004, 457-460, 1229-1232.	0.3	7
36	Highly linear 1–3 GHz GaN HEMT low-noise amplifier. , 2012, , .		7

#	ARTICLE	IF	CITATIONS
37	Characterization setup for device level dynamic load modulation measurements. , 2009, , .		5
38	An X-Band Low Phase Noise AlGaIn-GaN-HEMT MMIC Push-Push Oscillator. , 2011, , .		5
39	Dielectric loss determination of fine residual waste electrical and electronic equipment for understanding of heat development during microwave pyrolysis. Journal of Analytical and Applied Pyrolysis, 2013, 103, 142-148.	2.6	4
40	Design method for quasi-optimal multiband branch-line couplers. International Journal of RF and Microwave Computer-Aided Engineering, 2014, 24, 117-129.	0.8	4
41	Statistical estimation of the propagation constant in multilayer calibrations. , 2006, , .		3
42	Power amplifier behavioral modeling performance comparison of the LSNA and the modulation-domain system. , 2008, , .		3
43	Extending the Best Linear Approximation to Characterize the Nonlinear Distortion in GaN HEMTs. IEEE Transactions on Microwave Theory and Techniques, 2011, 59, 3087-3094.	2.9	3
44	Semi-physical nonlinear circuit model with device/physical parameters for HEMTs. International Journal of Microwave and Wireless Technologies, 2011, 3, 25-33.	1.5	3
45	SiC MESFET with a Double Gate Recess. Materials Science Forum, 2006, 527-529, 1227-1230.	0.3	2
46	Accuracy Improvement of Oscilloscope Based Modulated RF Measurements. , 2006, , .		2
47	High Power-Density 4H-SiC RF MOSFETs. Materials Science Forum, 2006, 527-529, 1277-1280.	0.3	1
48	Multi-line TRL calibration compared to a general de-embedding method. , 2009, , .		1
49	Uncertainties in small-signal equivalent circuit modeling. , 0, , 86-122.		1
50	A new baseband measurement system for characterization of memory effects in nonlinear microwave devices. , 2012, , .		1
51	Development of a Microstrip SiC MMIC Process. Materials Science Forum, 2006, 527-529, 1123-1126.	0.3	0
52	Influence of Passivation Oxide Properties on SiC Field-Plated Buried Gate MESFETs. Materials Science Forum, 2008, 600-603, 1103-1106.	0.3	0
53	Design and characterization of a highly linear 3 GHz GaN HEMT amplifier. , 2011, , .		0
54	Noise temperature of an electronic tuner for noise parameter measurement systems. , 2012, , .		0